

L Number	Hits	Search Text	DB	Time stamp
1	1	"10/080,539"	USPAT;	2004/06/10 15:59
2	100	kagoshima-akira.in. yamamoto-hideyuki.in. torii-yoshimi.in.	US-PGPUB	
3	31	(kagoshima-akira.in. yamamoto-hideyuki.in. torii-yoshimi.in.) and (control\$4 with etch\$3) and ash\$3	USPAT;	2004/06/10 16:00
4	0	(204/298.35.ccls. 204/298.25.ccls. 204/298.32.ccls.) and (etch\$3 same ash\$3 same control\$4 same (transfer\$4 transport\$4) same order)	USPAT;	2004/06/10 16:05
5	46	(204/298.35.ccls. 204/298.25.ccls. 204/298.32.ccls.) and (control\$4 same (transfer\$4 transport\$4) same order)	US-PGPUB	2004/06/10 16:07
6	3	(204/298.35.ccls. 204/298.25.ccls. 204/298.32.ccls.) and ((order near control\$4) same (transfer\$4 transport\$4))	USPAT;	2004/06/10 16:07
-	8	118/719.ccls. and (chamber with pressure with higher with prevent)	US-PGPUB	2004/06/10 16:08
-	1	("20010040145").PN.	USPAT;	2004/06/10 11:26
-	196	156/345.24	US-PGPUB	2003/02/26 10:13
-	600	((156/345.24) or (156/345.51) or (156/345.52) or (156/345.53)).CCLS.	USPAT;	2003/08/22 16:30
-	177	((156/345.24) or (156/345.51) or (156/345.52) or (156/345.53)).CCLS.) and (control\$3 with (substrate wafer target) with temperature)	US-PGPUB	2003/08/22 16:31
-	4	((156/345.24) or (156/345.51) or (156/345.52) or (156/345.53)).CCLS.) and (control\$3 with (substrate wafer target) with temperature)) and ((high with densit\$3) same (low with ion\$6))	USPAT;	2004/06/09 19:43
-	728	(156/345.\$CCLS.) and (control\$3 with (substrate wafer target) with temperature)	US-PGPUB	2003/08/22 17:14
-	142	(156/345.\$CCLS.) and (control\$3 with (substrate wafer target) with temperature with etch\$3)	USPAT;	2004/06/09 19:44
-	166	(156/345.\$CCLS.) and (control\$4 with (substrate wafer target) with temperature with etch\$3)	USPAT;	2004/06/09 19:44
-	131	(156/345.\$CCLS.) and (control\$4 with (substrate wafer target) with temperature with during with (process\$3 treatm\$3))	US-PGPUB	2004/06/09 19:46
-	2	(156/345.\$CCLS.) and (control\$4 with (substrate wafer target) with temperature with during with (process\$3 treatm\$3) with damag\$3)	USPAT;	2004/06/09 19:47
-	39	(control\$4 with (substrate wafer target) with temperature with during with (process\$3 treatm\$3) with damag\$3)	US-PGPUB	2004/06/09 19:56
-	0	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls. 204/298.25.ccls. 204/298.35.ccls.) and (156/345.24.ccls. 156/345.27.ccls. 204/298.03.ccls. 204/298.32.ccls.) and (control\$4 with (substrate wafer workpiece) with temperature with during with (process\$3 treatm\$3) with damag\$3)	USPAT;	2004/06/09 20:00
-	0	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls. 204/298.25.ccls. 204/298.35.ccls.) and (156/345.24.ccls. 156/345.27.ccls. 204/298.03.ccls. 204/298.32.ccls.) and (control\$4 with (substrate wafer workpiece) with temperature with damag\$3)	US-PGPUB	2004/06/09 20:00

-	79	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls. 204/298.25.ccls. 204/298.35.ccls.) and (156/345.24.ccls. 156/345.27.ccls. 204/298.03.ccls. 204/298.32.ccls.)	USPAT; US-PGPUB	2004/06/09 20:00
-	24	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls. 204/298.25.ccls. 204/298.35.ccls.) and (156/345.24.ccls. 156/345.27.ccls. 204/298.03.ccls. 204/298.32.ccls.) and (control\$4 with temperature)	USPAT; US-PGPUB	2004/06/09 20:11
-	0	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls. 204/298.25.ccls. 204/298.35.ccls.) and (156/345.24.ccls. 156/345.27.ccls. 204/298.03.ccls. 204/298.32.ccls.) and (control\$4 with temperature with magnet\$ with propert\$3)	USPAT; US-PGPUB	2004/06/09 20:12
-	1	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls. 204/298.25.ccls. 204/298.35.ccls.) and (control\$4 with temperature with magnet\$ with propert\$3)	USPAT; US-PGPUB	2004/06/09 20:12
-	3	(156/345.24.ccls. 156/345.27.ccls. 204/298.03.ccls. 204/298.32.ccls.) and (control\$4 with temperature with magnet\$ with propert\$3)	USPAT; US-PGPUB	2004/06/09 20:13
-	133	(control\$4 with temperature with magnet\$ with propert\$3)	EPO; JPO; DERWENT	2004/06/09 20:13
-	2	(control\$4 with temperature with magnet\$ with propert\$3 with (during) with (treat\$4 process\$4))	EPO; JPO; DERWENT	2004/06/09 20:14
-	11	(control\$4 with temperature with magnet\$ with propert\$3 with (during) with (treat\$4 process\$4))	USPAT; US-PGPUB	2004/06/09 20:20
-	65	(control\$4 with temperature with magnet\$ with propert\$3 with (treat\$4 process\$4))	USPAT; US-PGPUB	2004/06/09 20:20
-	65	(control\$4 with temperature with magnet\$ with propert\$3 with (treat\$4 process\$4))	USPAT; US-PGPUB	2004/06/09 20:21
-	24	(control\$4 with temperature with magnet\$ with propert\$3 with (treat\$4 process\$4))	EPO; JPO; DERWENT	2004/06/09 20:21
-	788	(156/345.\$ccls. 118/715/733.\$ccls.) and ((control\$4 with temperature) with (substrate wafer workpiece))	USPAT; US-PGPUB	2004/06/10 11:27
-	177	(156/345.\$ccls. 118/715/733.\$ccls.) and ((control\$4 with temperature) with (substrate wafer workpiece) with (during))	USPAT; US-PGPUB	2004/06/10 11:27
-	13	(156/345.\$ccls. 118/715/733.\$ccls.) and ((control\$4 adj temperature) adj (substrate wafer workpiece) adj (during))	USPAT; US-PGPUB	2004/06/10 13:13
-	22	(156/345.\$ccls.) and ((low adj temperature) adj (etch\$3))	USPAT; US-PGPUB	2004/06/10 13:14
-	10	("5571366" "5572366" "5645683" "5695564" "5695654" "5700734" "5756401" "6008139" "6046116" "6087264").PN.	USPAT	2004/06/10 13:17
-	18	(156/345.\$ccls. 216/\$ccls.) and (plasma same (low adj ion adj energy) same (high adj density))	USPAT; US-PGPUB	2004/06/10 15:53